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Triacs

BT136 series

GENERAL DESCRIPTION

Glass passivated triacs in a plastic envelope, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

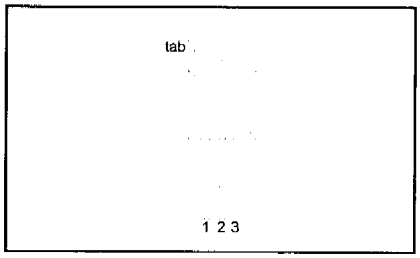
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
	BT136-	**500**	**600**	**800**	
	BT136-	**500F**	**600F**	**800F**	
	BT136-	**500G**	**600G**	**800G**	
V_{DRM}	Repetitive peak off-state voltages	500	600	800	V
$I_{T(RMS)}$	RMS on-state current	4	4	4	A
I_{TSM}	Non-repetitive peak on-state current	25	25	25	A

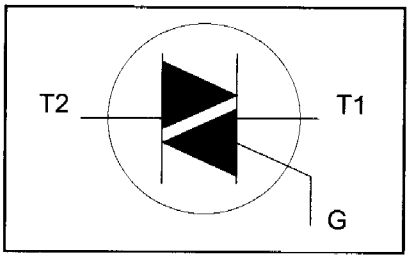
PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
				-500	**-600**	**-800**	
V_{DRM}	Repetitive peak off-state voltages		-	500[1]	600[1]	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 107$ °C	-	4			A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_j = 25$ °C prior to surge					
		t = 20 ms	-	25			A
		t = 16.7 ms	-	27			A
I^2t	I^2t for fusing	t = 10 ms	-	3.1			A^2s
dI_T/dt	Repetitive rate of rise of on-state current after triggering	I_{TM} = 6 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs					
		T2+ G+	-	50			A/µs
		T2+ G-	-	50			A/µs
		T2- G-	-	50			A/µs
		T2- G+	-	10			A/µs
I_{GM}	Peak gate current		-	2			A
V_{GM}	Peak gate voltage		-	5			V
P_{GM}	Peak gate power		-	5			W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5			W
T_{stg}	Storage temperature		-40	150			°C
T_j	Operating junction temperature		-	125			°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base	full cycle	-	-	3.0	K/W
		half cycle	-	-	3.7	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	in free air	-	60	-	K/W

STATIC CHARACTERISTICS

T_j = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.			UNIT
		BT136-			...	...F	...G	
I_{GT}	Gate trigger current	V_D = 12 V; I_T = 0.1 A						
		T2+ G+	-	5	35	25	50	mA
		T2+ G-	-	8	35	25	50	mA
		T2- G-	-	11	35	25	50	mA
		T2- G+	-	30	70	70	100	mA
I_L	Latching current	V_D = 12 V; I_{GT} = 0.1 A						
		T2+ G+	-	7	20	20	30	mA
		T2+ G-	-	16	30	30	45	mA
		T2- G-	-	5	20	20	30	mA
		T2- G+	-	7	30	30	45	mA
I_H	Holding current	V_D = 12 V; I_{GT} = 0.1 A	-	5	15	15	30	mA
V_T	On-state voltage	I_T = 5 A	-	1.4	1.70			V
V_{GT}	Gate trigger voltage	V_D = 12 V; I_T = 0.1 A	-	0.7	1.5			V
		V_D = 400 V; I_T = 0.1 A; T_j = 125 °C	0.25	0.4	-			V
I_D	Off-state leakage current	V_D = $V_{DRM(max)}$; T_j = 125 °C	-	0.1	0.5			mA

DYNAMIC CHARACTERISTICS

T_j = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.			TYP.	MAX.	UNIT
		BT136-	...	...F	...G			
dV_D/dt	Critical rate of rise of off-state voltage	V_{DM} = 67% $V_{DRM(max)}$; T_j = 125 °C; exponential waveform; gate open circuit	100	50	200	250	-	V/µs
dV_{com}/dt	Critical rate of change of commutating voltage	V_{DM} = 400 V; T_j = 95 °C; $I_{T(RMS)}$ = 4 A; dI_{com}/dt = 1.8 A/ms; gate open circuit	-	-	10	50	-	V/µs
t_{gt}	Gate controlled turn-on time	I_{TM} = 6 A; V_D = $V_{DRM(max)}$; I_G = 0.1 A; dI_G/dt = 5 A/µs	-	-	-	2	-	µs